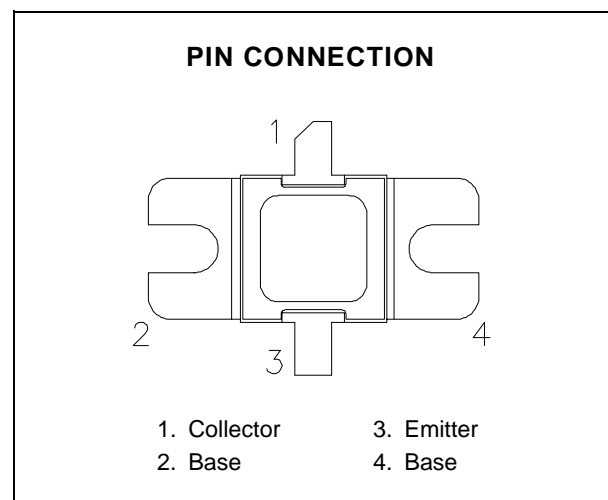
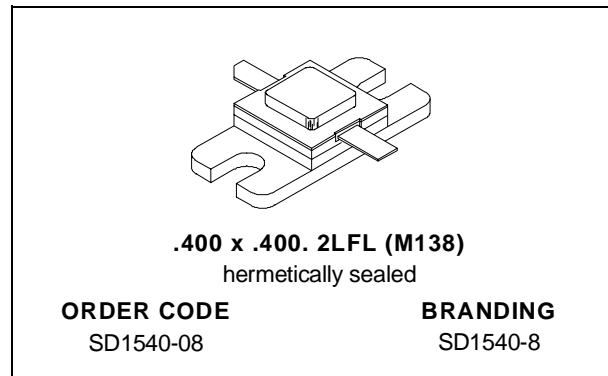


**RF & MICROWAVE TRANSISTORS  
AVIONICS APPLICATIONS**

- DESIGNED FOR HIGH POWER PULSED IFF, DME, TACAN APPLICATIONS
- 350 WATTS (typ.) IFF 1030 - 1090 MHz
- 300 WATTS (min.) DME 1025 - 1150 MHz
- 290 WATTS (typ.) TACAN 960 - 1215 MHz
- 6.3 dB MIN. GAIN
- REFRACTORY GOLD METALLIZATION
- EMITTER BALLASTING AND LOW THERMAL RESISTANCE FOR RELIABILITY AND RUGGEDNESS
- 20:1 LOAD VSWR CAPABILITY AT SPECIFIED OPERATING CONDITIONS
- INPUT/OUTPUT MATCHED, COMMON BASE CONFIGURATION


**DESCRIPTION**

The SD1540-08 is a gold metallized silicon, NPN power transistor designed for applications requiring high peak power and low duty cycles such as IFF, DME and TACAN. The SD1540 is packaged in a metal/ceramic package with internal input/output matching resulting in improved broadband performance and a low thermal resistance.

**ABSOLUTE MAXIMUM RATINGS** ( $T_{case} = 25^{\circ}C$ )

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	65	V
$V_{CES}$	Collector-Emitter Voltage	65	V
$V_{EBO}$	Emitter-Base Voltage	3.5	V
$I_C$	Device Current	22	A
$P_{DISS}$	Power Dissipation	875	W
$T_J$	Junction Temperature	+200	$^{\circ}C$
$T_{STG}$	Storage Temperature	- 65 to +150	$^{\circ}C$

**THERMAL DATA**

$R_{TH(j-c)}$	Junction-Case Thermal Resistance	0.20	$^{\circ}C/W$
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# SD1540-08

## ELECTRICAL SPECIFICATIONS (T<sub>case</sub> = 25°C)

### STATIC

Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
BV <sub>CBO</sub>	I <sub>C</sub> = 10mA	I <sub>E</sub> = 0mA	65	—	—	V
BV <sub>CES</sub>	I <sub>C</sub> = 25mA	V <sub>BE</sub> = 0V	65	—	—	V
BV <sub>EBO</sub>	I <sub>E</sub> = 5mA	I <sub>C</sub> = 0mA	3.5	—	—	V
I <sub>CES</sub>	V <sub>CE</sub> = 50V	I <sub>E</sub> = 0mA	—	—	25	mA
h <sub>FE</sub>	V <sub>CE</sub> = 5V	I <sub>C</sub> = 1A	10	—	—	—

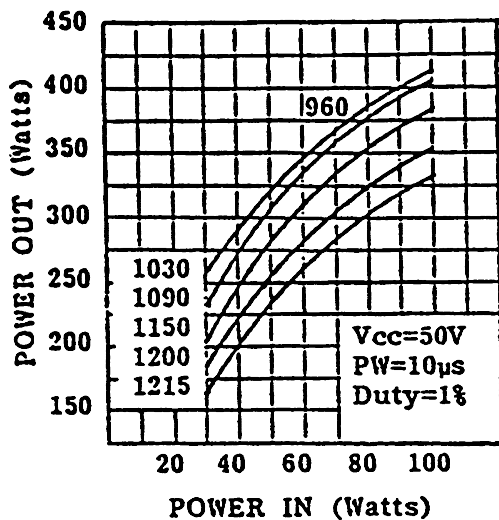
### DYNAMIC

Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
P <sub>OUT</sub>	f = 1025 — 1150MHz	P <sub>IN</sub> = 70 W V <sub>CE</sub> = 50 V	300	—	—	W
G <sub>P</sub>	f = 1025 — 1150MHz	P <sub>IN</sub> = 70 W V <sub>CE</sub> = 50 V	6.3	—	—	dB
η <sub>C</sub>	f = 1025 — 1150MHz	P <sub>IN</sub> = 70 W V <sub>CE</sub> = 50 V	35	—	—	%

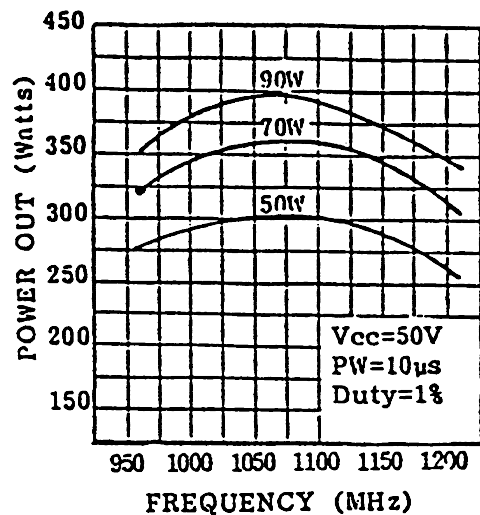
Note: Pulse Width = 10μSec, Duty Cycle = 1%  
 This device is suitable for use under other pulse width/duty cycle conditions.  
 Please contact the factory for specific applications assistance.

### TYPICAL PERFORMANCE

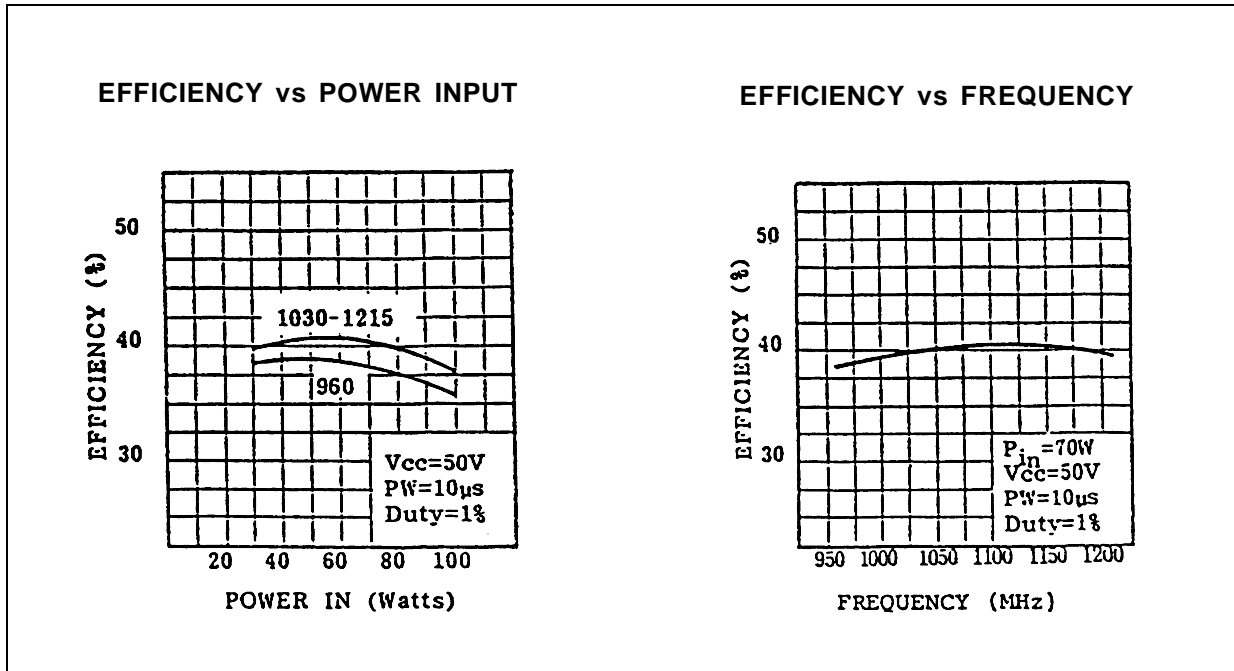
POWER OUTPUT vs POWER INPUT



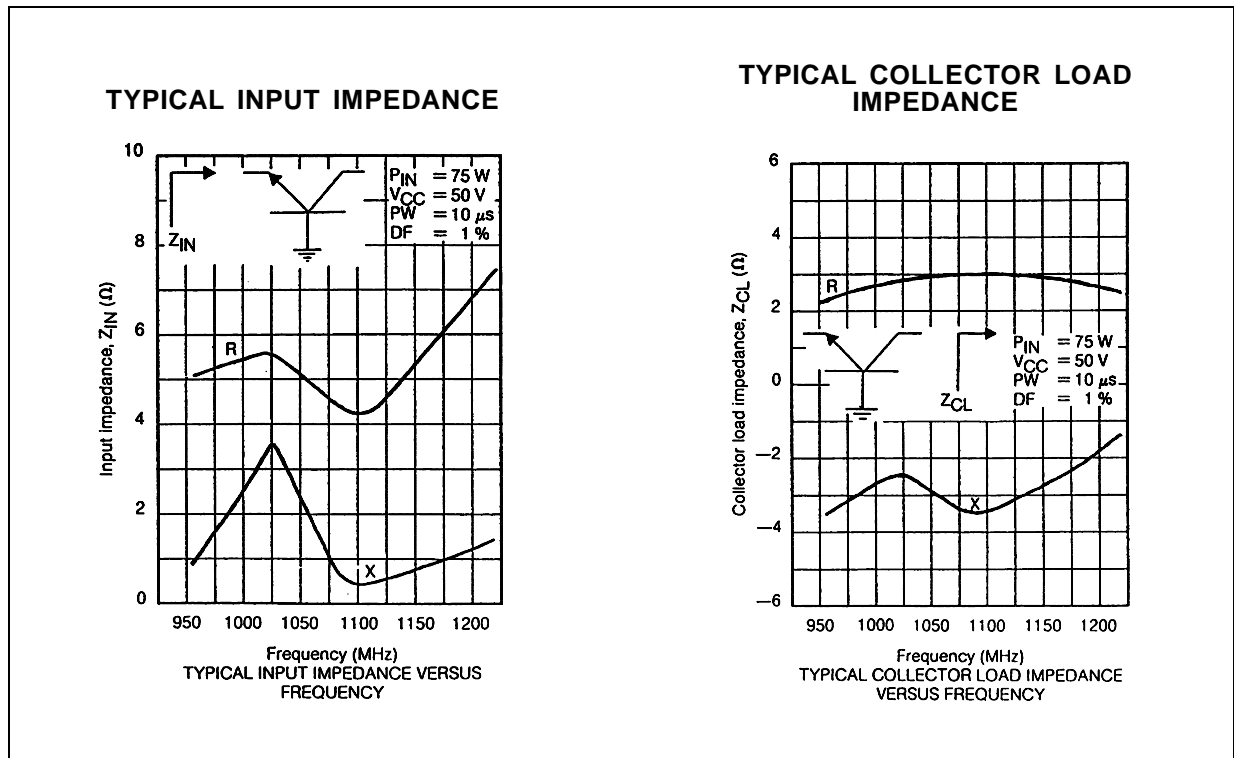
POWER OUTPUT vs FREQUENCY



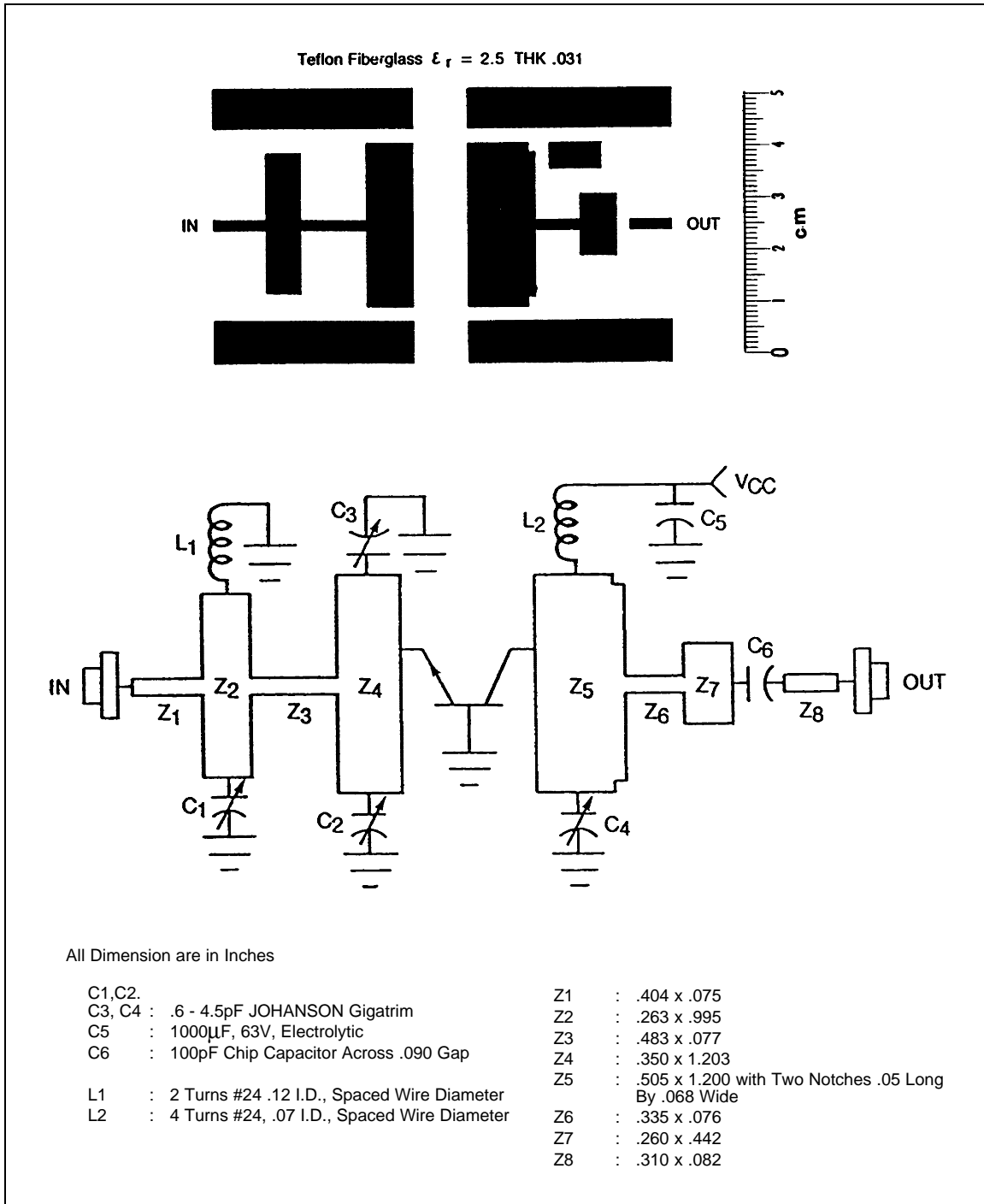
TYPICAL PERFORMANCE (cont'd)



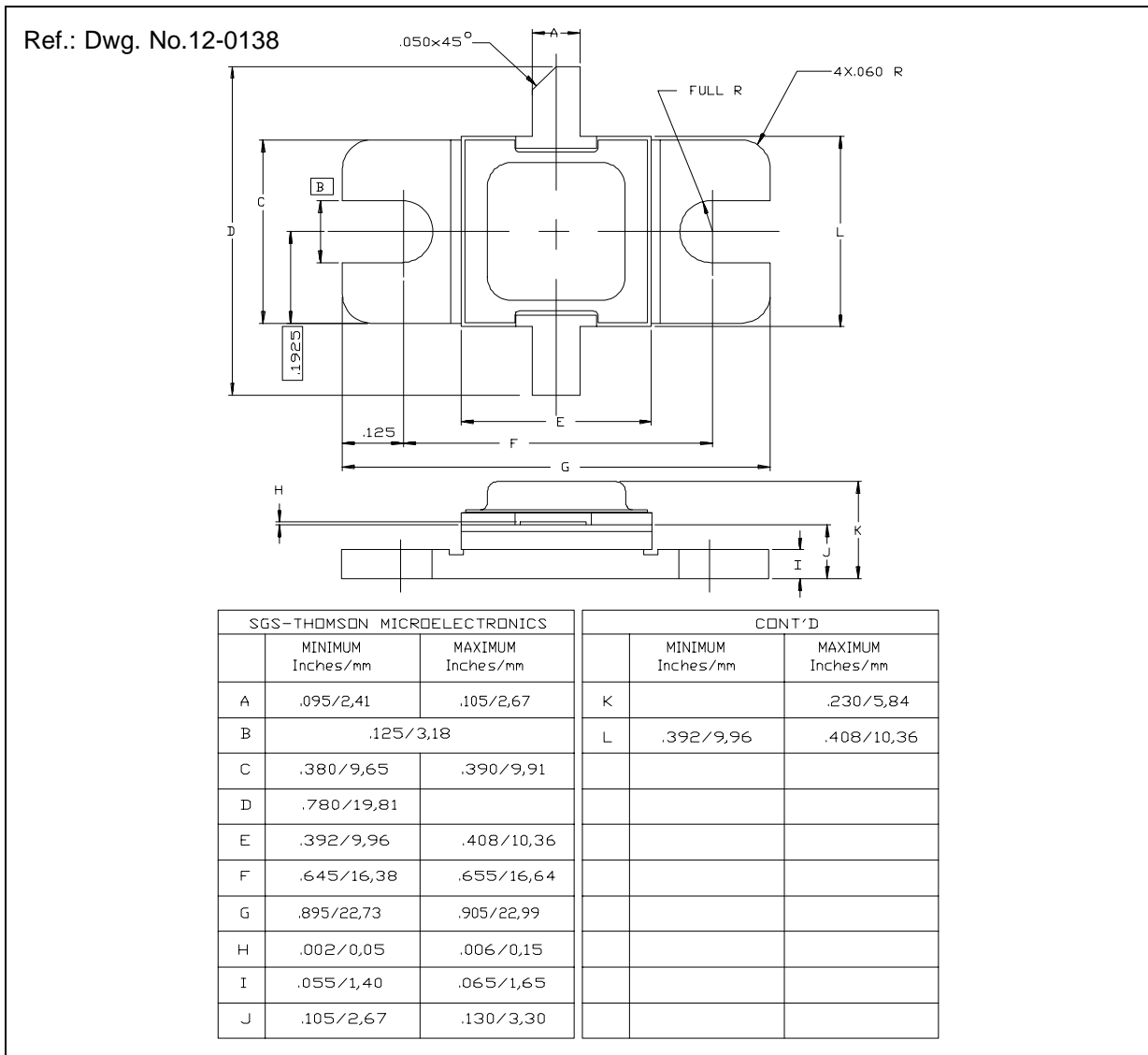
IMPEDANCE DATA



TEST CIRCUIT



## PACKAGE MECHANICAL DATA



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